

#### **Quad 2-Input NAND Gates in bare die form**

Rev 1.0 23/11/19

#### Description

74ALS00 provides x4 independent 2-input NAND gates performing the Boolean function Y =  $\overline{A \cdot B}$  or Y =  $\overline{A} + \overline{B}$ . The device is fabricated using a 1.5µm 40V Bipolar process. Internal circuitry comprises of 3 stages and includes buffered outputs for high noise immunity and stability. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

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## **Ordering Information**

The following part suffixes apply:

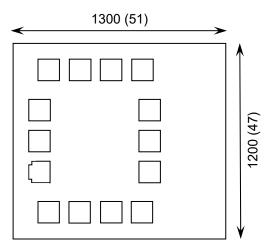
No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see 54ALS00

#### Features:

- High speed 3ns (Min) propagation delay
- Direct drop-in replacement for obsolete components in long term programs.

## Die Dimensions in µm (mils)



## **Supply Formats:**

- Default Die in Waffle Pack (300 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

#### **Mechanical Specification**

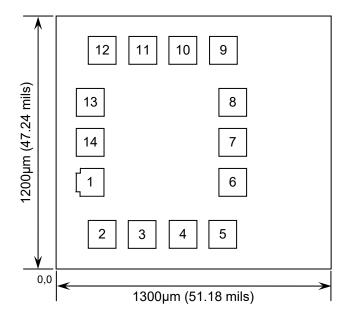
Die Size (Unsawn)	1300 x 1200 51 x 47	µm mils	
Minimum Bond Pad Size	130 x 130 5.12 x 5.12	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils	
Top Metal Composition	Al 1%Si 1.1μm		
Back Metal Composition	N/A – Bare Si		





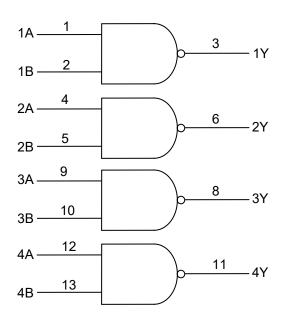
#### Rev 1.0 23/11/19

## Pad Layout and Functions



PAD	FUNCTION	COORDINATES (mm)			
PAD	FUNCTION	X	Y		
1	1A	0.100	0.345		
2	1B	0.155	0.100		
3	1Y	0.345	0.100		
4	2A	0.535	0.100		
5	2B	0.725	0.100		
6	2Y	0.770	0.345		
7	GND	0.770	0.535		
8	3Y	0.770	0.725		
9	3A	0.725	0.970		
10	3B	0.535	0.970		
11	4Y	0.345	0.970		
12	4A	0.155	0.970		
13	4B	0.100	0.725		
14	V <sub>CC</sub>	0.100	0.535		
CONNECT CHIP BACK TO GND OR FLOAT					

## Logic Diagram



## **Function Table**

INPL	INPUTS					
Α	В Ү					
L	L	Н				
L	H H					
Н	L	Н				
Н	H					
H = High level (steady state) L = Low level (steady state)						





Rev 1.0 23/11/19

## Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage	V <sub>CC</sub>	7.0	V
DC Input Voltage	V <sub>IN</sub>	7.0	V
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

### **Recommended Operating Conditions**

PARAMETER	SYMBOL	MIN	MAX	UNITS
Supply Voltage	V <sub>CC</sub>	4.5	5.5	V
High-Level Input Voltage	V <sub>IH</sub>	2	-	V
Low-Level Input Voltage	V <sub>IL</sub>	-	0.8	V
High-Level Output Current	I <sub>OH</sub>	-	-0.4	mA
Low-Level Output Current	I <sub>OL</sub>	-	8	mA
Operating Temperature Range	T <sub>J</sub>	-40	+85	°C

## DC Electrical Characteristics<sup>2</sup> T<sub>J</sub> = -40°C to 85°C unless otherwise specified

PARAMETER	SYMBOL	CONDITIONS		LIMITS			UNITS
TANAMETER	STINDOL			MIN	TYP	MAX	ONTO
Minimum High-Level Input Voltage	V <sub>IH</sub>	-		2	-	-	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>	-		-	-	0.8	V
Input Clamp Diode Voltage	V <sub>IK</sub>	V <sub>CC</sub> = MIN I <sub>IN</sub> = -18mA		-	-	-1.5	V
Output Voltage High	V <sub>OH</sub>	$V_{CC} = 4.5V \text{ to } 5.5V,$ $I_{OH} = -0.4\text{mA}$		V <sub>CC</sub> -2	-	-	V
Output Voltage Low V <sub>OL</sub>	V <sub>OL</sub>	V <sub>CC</sub> = 4.5V	I <sub>OL</sub> = 4mA	-	0.25	0.4	V
Output Voltage Low	V OL	I <sub>OL</sub> = 8mA	-	0.35	0.5	<b>'</b>	
Input Current	I <sub>IN</sub>	$V_{CC} = 5.5V, V_{IN} = 7V$		-	-	0.1	mA
Input High Current	I <sub>IH</sub>	$V_{CC} = 5.5V, V_{IN} = 2.7V$		-	-	20	μA
Input Low Current	I <sub>IL</sub>	$V_{CC} = 5.5, V_{IN} = 0.4V$		-	-	-0.1	mA
Output Current <sup>3</sup>	Io	$V_{CC} = 5.5, V_{OUT} = 2.25V$		-30	-	-112	mA
Power Supply	I <sub>CCH</sub>	$V_{CC} = 5.5V$ ,	V <sub>IN</sub> = 4.5V	-	0.5	0.85	mA
Current (Total)	I <sub>CCL</sub>	$V_{CC} = 5.5V$ ,	$V_{IN} = 0V$	-	1.5	3	111/-1

**<sup>2</sup>**. All typical values @  $V_{CC} = 5V$ ,  $T_J = 25$ °C.

<sup>3.</sup> Output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, Ios





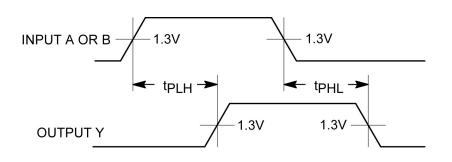
**Rev 1.0** 23/11/19

## AC Electrical Characteristics <sup>4</sup> T<sub>J</sub> = -55°C to 125°C unless otherwise specified

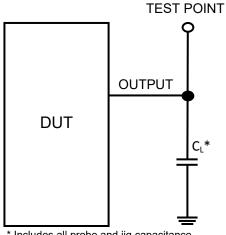
PARAMETER	SYMBOL CONDITIONS	LIMITS			UNITS	
.,	01111202		MIN	TYP	MAX	
Propagation Delay,	t <sub>PLH</sub>	$V_{CC}$ = 4.5 to 5.5V,	3	-	11	ns
A or B to output Y	t <sub>PHL</sub>	$C_L = 50 pF, R_L = 500 \Omega$	2	-	8	113

<sup>4.</sup> Not production tested in die form, characterized by chip design and tested in package.

## Switching Waveform



#### **Test Circuit**



\* Includes all probe and jig capacitance

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